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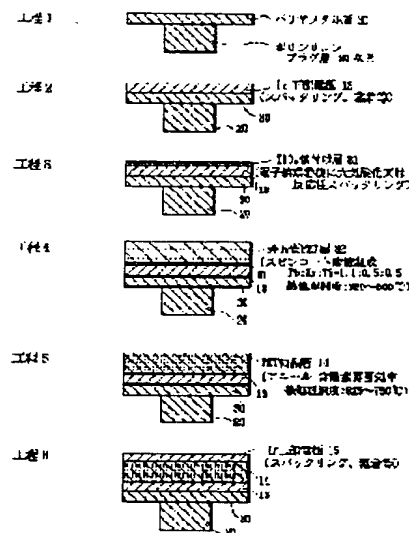
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(54) METHOD FOR MANUFACTURING FERROELECTRICS CAPACITOR AND METHOD
 FOR MANUFACTURING FERROELECTRICS MEMORY DEVICE

(57)Abstract:

PROBLEM TO BE SOLVED: To manufacture a ferroelectrics capacitor wherein all such important conditions as selection of optimum electrode material, control of crystal growth direction and optimum anneal temperature are met, with no polarization fatigue.

SOLUTION: At the interface between an iridium lower part electrode 13 and a PZT (lead zirconate titanate) thin film 14, a TiOx nucleus-adding layer 31 is deposited, and on the lower part electrode 13 where the oxide was deposited, a material layer 32 which contains an excessive specific component (especially a lead) of the PZT thin film 4 is formed, and it is thermal treated at a temperature where a surface precipitation material (especially a structure transition layer) whose main component is the specific component substantially disappears, for forming the PZT thin film 14.



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